

J308, J309, J310 N-Channel JFET

Features

- InterFET [N0072L Geometry](#)
- Low Noise: 2 nV/VHz Typical
- Low Ciss: 4pF Typical
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

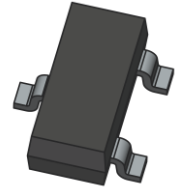
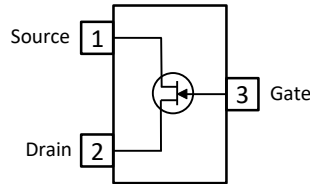
Applications

- Mixers
- Oscillators
- VHF/UHF Amplifiers

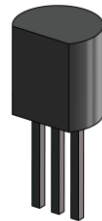
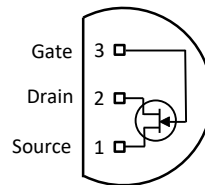
Description

The -25V InterFET J308, J309, and J310 are targeted for higher gain VHF amplifiers, mixers, and oscillators. Gate leakages are typically less than 10pA at room temperatures.

SOT23 Top View



TO-92 Bottom View



Product Summary

| Parameters | J308 Min | J309 Min | J310 Min | Unit |
|---|----------|----------|----------|------|
| BV _{GSS} Gate to Source Breakdown Voltage | -25 | -25 | -25 | V |
| I _{DSS} Drain to Source Saturation Current | 12 | 12 | 24 | mA |
| V _{GS(off)} Gate to Source Cutoff Voltage | -1 | -1 | -2 | V |
| G _{FS} Forward Transconductance | 8 | 10 | 8 | mS |

Ordering Information Custom Part and Binning Options Available

| Part Number | Description | Case | Packaging |
|---------------------------------|---|-------|---------------------------------------|
| J308; J309; J310 | Through-Hole | TO-92 | Bulk |
| SMPJ308; SMPJ309; SMPJ310 | Surface Mount | SOT23 | Bulk |
| SMPJ308TR; SMPJ309TR; SMPJ310TR | 7" Tape and Reel: Max 3,000 Pieces 13" Tape and Reel: Max 9,000 Pieces | SOT23 | Minimum 1,000 Pieces Tape and Reel |
| J308COT; J309COT; J310COT | Chip Orientated Tray (COT Waffle Pack) | COT | 400/Waffle Pack |
| J308CFT; J309CFT; J310CFT | Chip Face-up Tray (CFT Waffle Pack) | CFT | 400/Waffle Pack |



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.

Electrical Characteristics

Maximum Ratings (@ $T_A = 25^\circ\text{C}$, Unless otherwise specified)

| Parameters | Value | Unit |
|--|------------|----------------------|
| V_{RGS} Reverse Gate Source and Gate Drain Voltage | -25 | V |
| I_{FG} Continuous Forward Gate Current | 10 | mA |
| P_D Continuous Device Power Dissipation | 360 | mW |
| P Power Derating | 3.27 | mW/ $^\circ\text{C}$ |
| T_J Operating Junction Temperature | -55 to 125 | $^\circ\text{C}$ |
| T_{STG} Storage Temperature | -65 to 150 | $^\circ\text{C}$ |

Static Characteristics (@ $T_A = 25^\circ\text{C}$, Unless otherwise specified)

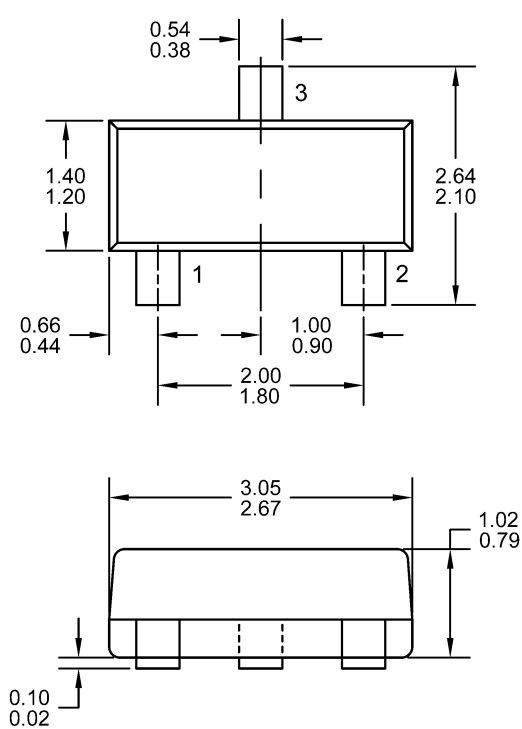
| Parameters | Conditions | J308 | | | J309 | | | J310 | | | Unit |
|--|---|------|-----|------|------|-----|-----|------|-----|------|---------------------|
| | | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max | |
| $V_{(BR)GSS}$ Gate to Source Breakdown Voltage | $V_{DS} = 0V, I_G = -1\mu\text{A}$ | -25 | | | -25 | | | -25 | | | V |
| I_{GSS} Gate to Source Reverse Current | $V_{GS} = -15V, V_{DS} = 0V, T_A = 25^\circ\text{C}$ $V_{GS} = -15V, V_{DS} = 0V, T_A = 125^\circ\text{C}$ | | | -1 | | | -1 | | | -1 | nA μA |
| $V_{GS(OFF)}$ Gate to Source Cutoff Voltage | $V_{DS} = 10V, I_D = 1\text{nA}$ | -1 | | -6.5 | -1 | | -4 | -2 | | -6.5 | V |
| $V_{GS(F)}$ Gate to Source Forward Voltage | $V_{DS} = 0V, I_G = 1\text{mA}$ | | | 1 | | | 1 | | | 1 | V |
| I_{DSS} Drain to Source Saturation Current | $V_{GS} = 0V, V_{DS} = 10V$ (Pulsed) | 12 | | 60 | 12 | | 30 | 24 | | 60 | mA |

Dynamic Characteristics (@ $T_A = 25^\circ\text{C}$, Unless otherwise specified)

| Parameters | Conditions | J308 | | | J309 | | | J310 | | | Unit |
|--|--|------|-----|-----|------|-----|-----|------|-----|-----|------------------------|
| | | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max | |
| G_{FS} Forward Transconductance | $V_{DS} = 10V, I_D = 10\text{mA}, f = 1\text{kHz}$ | 8 | 17 | | 10 | 17 | | 8 | 17 | | mS |
| G_{OS} Output Conductance | $V_{DS} = 10V, I_D = 10\text{mA}, f = 1\text{kHz}$ | | | 250 | | | 250 | | | 250 | μS |
| G_{FG} Gate Forward Transconductance | $V_{DS} = 10V, I_D = 10\text{mA}, f = 1\text{kHz}$ | | 13 | | | 13 | | | 1.2 | | mS |
| G_{OG} Gate Output Transconductance | $V_{DS} = 10V, I_D = 10\text{mA}, f = 1\text{kHz}$ | | 150 | | | 100 | | | 150 | | μS |
| C_{dg} Drain Capacitance | $V_{DS} = 0V, V_{GS} = -10V, f = 1\text{MHz}$ | | 1.8 | 2.5 | | 1.8 | 2.5 | | 1.8 | 2.5 | pF |
| C_{gs} Source Capacitance | $V_{DS} = 0V, V_{GS} = -10V, f = 1\text{MHz}$ | | 4 | 5 | | 4 | 5 | | 4 | 5 | pF |
| e_n Noise Voltage | $V_{DS} = 10V, I_D = 10\text{mA}, f = 100\text{kHz}$ | | | 10 | | | 10 | | | 10 | nV/ $\sqrt{\text{Hz}}$ |
| NF Noise Figure | $V_{DS} = 15V, I_D = 10\text{mA}, f = 105\text{MHz}$ $V_{DS} = 15V, I_D = 10\text{mA}, f = 450\text{MHz}$ | | 1.5 | | | 1.5 | | | 1.5 | | dB |
| | | | 2.7 | | | 2.7 | | | 2.7 | | |

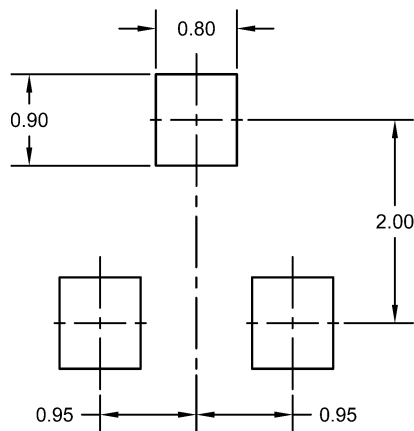
SOT23 (TO-236AB) Mechanical and Layout Data

Package Outline Data



1. All linear dimensions are in millimeters.
2. Package weight approximately 0.12 grams
3. Molded plastic case UL 94V-0 rated
4. For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
5. Bulk product is shipped in standard ESD shipping material
6. Refer to JEDEC standards for additional information.

Suggested Pad Layout



1. All linear dimensions are in millimeters.
2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.